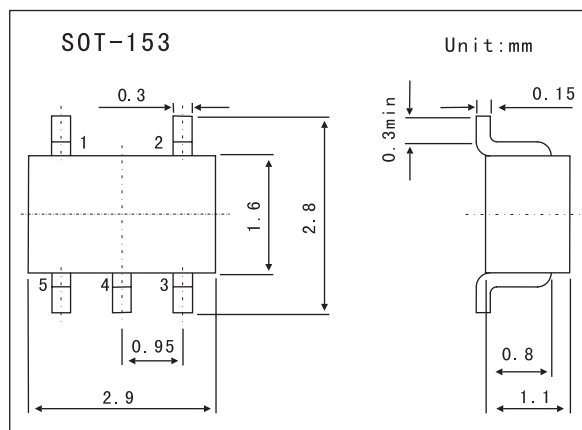


FMA1A

■ Features

- Mounting Cost and Area Can Be Cut In Half.
- Emitter-common Type.
- PNP Epitaxial Planar Silicon Transistor.



■ Absolute Maximum Ratings Ta = 25°C

< For Tr1 and Tr2 in common >

| Parameter | Symbol | Rating | Unit |
|----------------------|---------------------|-------------|------|
| Supply Voltage | V _{CC} | -50 | V |
| Input Voltage | V _{IN} | -40 to +10 | V |
| Output Current | I _O | -30 | mA |
| Collector Current | I _{C(Max)} | -100 | |
| Power Dissipation | P _D * | 300 | mW |
| Junction temperature | T _j | 150 | °C |
| Storage temperature | T _{stg} | -55 to +150 | °C |

* 200mW per element must not be exceeded.

■ Electrical Characteristics Ta = 25°C

< For Tr1 and Tr2 in common >

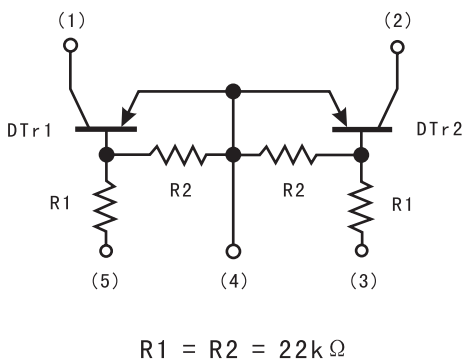
| Parameter | Symbol | Testconditions | Min | Typ | Max | Unit |
|-----------------------|--------------------------------|--|------|------|-------|------|
| Input Voltage | V _{I(off)} | V _{CC} = -5V , I _O = -100 μ A | | | -0.5 | V |
| | V _{I(on)} | V _O = -0.2V , I _O = -5mA | -3 | | | |
| Output Voltage | V _{O(on)} | I _O /I _I = -10mA/-0.5mA | | -0.1 | -0.3 | V |
| Input Current | I _I | V _I = -5V | | | -0.36 | mA |
| Output Current | I _{O(off)} | V _{CC} = -50V , V _I = 0V | | | -0.5 | μ A |
| DC Current Gain | G _I | V _O = -5V , I _O = -5mA | 56 | | | |
| Input Resistance | R ₁ | | 15.4 | 22 | 28.6 | k Ω |
| Resistance Ratio | R ₂ /R ₁ | | 0.8 | 1 | 1.2 | |
| Transistion Frequency | f _r * | V _{CE} = -10V , I _E = 5mA , f = 100MHz | | 250 | | MHz |

* Characteristics of built-in transistor

■ Marking

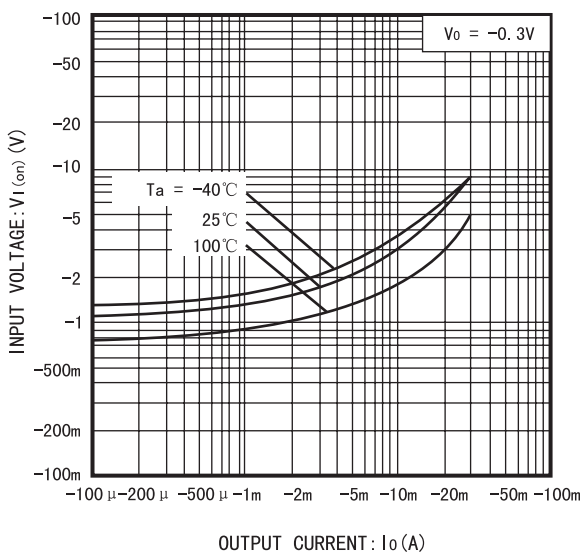
| | |
|---------|----|
| Marking | A1 |
|---------|----|

■ Equivalent Circuit

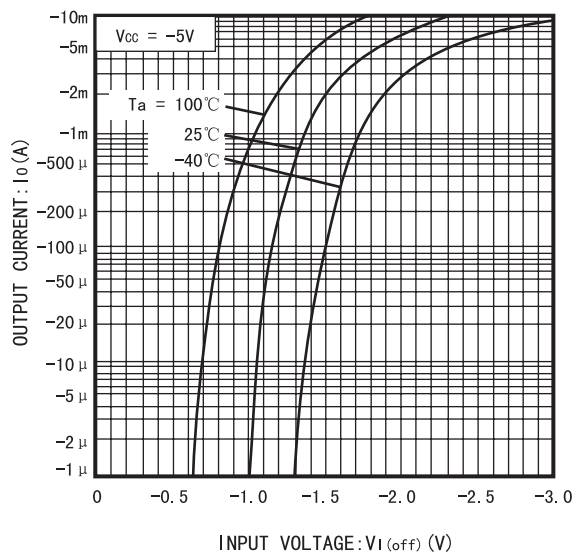


- (1) OUT
- (2) OUT
- (3) IN
- (4) GND
- (5) IN

■ Electrical Characteristics Curves



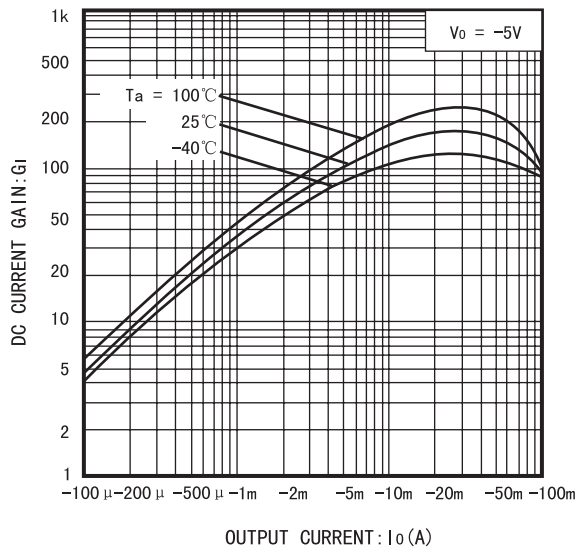
Input voltage vs. output current
(ON characteristics)



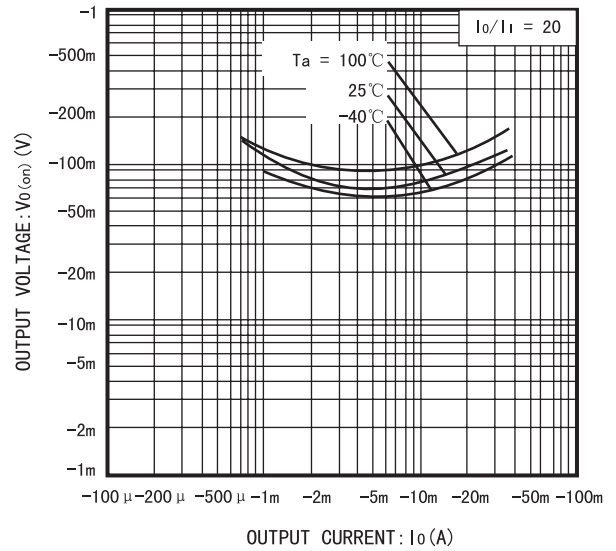
Output current vs. input voltage
(OFF characteristics)



FMA1A



DC current gain vs. Output current



Output voltage vs. Output current